ABSTRACT

A semiconductor device includes: first and second channel structures spaced apart from each other in a first direction; and a source/drain pattern, between the first and second channel structures, including a first interface contacting the first channel structure and a second interface contacting the second channel structure, wherein, in a plan view, the source/drain pattern includes first and second side walls opposite to each other in a second direction, the first side wall includes a first sloped side wall, a second sloped side wall, and a first horizontal intersection at which the first and second sloped side walls meet, a width of the first interface is different from a width of the second interface, in the second direction, and a distance from the first interface to the first horizontal intersection is greater than a distance from the second interface to the first horizontal intersection, in the first direction.

FIG. 8